

said voltage reception device is configured to couple to said memory circuit; and  
said voltage reception device is selectively electrically communicative with a first test voltage path and a second test voltage path;  
and wherein said voltage reception device is configured to electrically interpose between said equilibration device and said digit line pair.

A marked version of these amended claims appears in an appendix to this Preliminary Amendment.

Please add the following claims.

139. (New) A method of regulating a control device within a non-static semiconductor device, comprising:

coupling said control device to a sense amplifier within said semiconductor device;  
driving said control device with a first voltage;  
performing a first test on said sense amplifier;  
driving said control device with a second voltage; and  
performing a second test on said sense amplifier.

140. (New) The method in claim 139, wherein said step of coupling comprises coupling said control device to a sense amplifier within a dynamic semiconductor device.

141. (New) The method in claim 140, wherein said step of coupling comprises coupling said control device to a sense amplifier within a dynamic random access memory.

142. (New) A method of regulating a control device for complementary data lines within a semiconductor device, comprising:

amplifying a voltage difference between said complementary data lines using said control device being driven at a first voltage; and  
amplifying a voltage difference between said complementary data lines using said

control device being driven at a second voltage.

143. (New) A method of regulating a transistor coupling a sense amplifier to a voltage node, comprising:

- driving said transistor with a first voltage;
- testing said sense amplifier with said transistor driven at said first voltage;
- driving said transistor with a second voltage; and
- testing said sense amplifier with said transistor driven at said second voltage.

144. (New) A method of regulating a transistor within a semiconductor device, comprising:

- driving said transistor with a first voltage, wherein said step of driving said transistor with a first voltage comprises driving a bleeder device;
- testing said semiconductor device with said transistor driven at said first voltage;
- driving said transistor with a second voltage; and
- testing said semiconductor device with said transistor driven at said second voltage.

145. (New) A method of regulating a transistor within a semiconductor device, comprising:

- driving said transistor with a first voltage, wherein said step of driving said transistor with a first voltage comprises driving a voltage-pulling transistor of a sense amplifier;
- testing said semiconductor device with said transistor driven at said first voltage;
- driving said transistor with a second voltage; and
- testing said semiconductor device with said transistor driven at said second voltage.

146. (New) The method in claim 145, wherein said step of driving a voltage-pulling transistor comprises driving a pulldown transistor.

147. (New) The method in claim 145, wherein said step of driving a voltage-pulling transistor comprises driving a pullup transistor.

148. (New) A method of regulating a device for a sense amplifier, comprising: